

TRANSMITTAL OF FORMAL DRAWINGSDocket No.
00750452AAIn Re Application Of: **Park et al.**

JAN 08 2004

Serial No.

09/924,318

Filing Date

08/08/2001

Confirmation No.

3592

Examiner

B. Tran

Art Unit

1765

Invention: **METHOD OF BUILDING A CMOS STRUCTURE ON THIN SOI WITH SOURCE/DRAIN ELECTRODES FORMED BY IN SITU DOPED SELECTIVE AMORPHOUS SILICON**Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Transmitted herewith are:

4 sheets of formal drawing(s) for this application.

☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).

This submission of formal drawings is in response to the Notice of Allowability mailed on January 5, 2004.



Signature

Marshall M. Curtis**Reg. No. 33.138**Whitham, Curtis & Christofferson, P.C.
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Reston, VA 20190
(703) 787-9400
Customer Number 30743Dated: **January 8, 2004**

I certify that this document and attached formal drawings are being deposited on _____ with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signature of Person Mailing Correspondence

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